



# 700 MHz, - 3 dB Bandwidth; Dual SPDT Analog Switch

#### **DESCRIPTION**

DG2723 is a low R<sub>ON</sub>, high bandwidth analog switch configured in dual SPDT. It achieves 7  $\Omega$  switch on resistance, greater than 700 MHz - 3 dB bandwidth with 5 pF load, and a channel to channel crosstalk and isolation at - 49 dB. Fabricated with high density sub micro CMOS process, the DG2723 provides low parasitic capacitance. handles bidirectional signal flow with minimized phase distortion. Guaranteed 1.3 V logic high threshold makes it possible to interface directly with low voltage MCUs. The DG2723 is designed for a wide range of operating voltages from 2.7 V to 4.3 V that can be driven directly from one cell Li-ion battery. On-chip protection circuit protects again fault events when signals at "com" pins goes beyond V+.

Latch up current is 300 mA, as per JESD78, and its ESD tolerance exceeds 8 kV. Packaged in ultra small miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm), it is ideal for portable high speed mix signal switching application.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The miniQFN-10 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix to the ordering part number. The nickel-palladium-gold device terminations meet all JEDEC standards for reflow and MSL rating. As a further sign of Vishay Siliconix's commitment, the DG2723 is fully RoHS complaint.

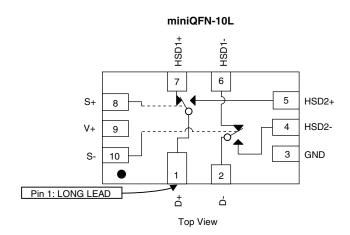
#### **FEATURES**

- Wide operation voltage range
- Low on-resistance, 7  $\Omega$  (typical at 3 V)
- Low capacitance, 5.6 pF (typical)
- 3 dB high bandwidth with 5pF load: 700 MHz (typical)
- · Low bit to bit skew: 40 pS (typical)
- Low power consumption
- Low logic threshold: V
- Power down protection: D+/D- pins can tolerate up to 5 V when V+=0 V
- Logic (S+ and S-) above V+ tolerance
- 8 kV ESD protection (HBM)
- Latch-up current 300 mA per JESD78
- Lead (Pb)-free low profile miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm)
- Compliant to RoHS Directive 2002/95/EC

## **APPLICATIONS**

- Cellular phones
- Portable media players
- PDA
- Digital camera
- **GPS**
- Notebook computer
- TV, monitor, and set top box

### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**



Document Number: 68767 S11-2216-Rev. B, 14-Nov-11



ORDERING INFORMATION						
Temp. Range	Package	Part Number				
- 40 °C to 85 °C	miniQFN-10	DG2723DN-T1-E4				

TRUTH TABLE					
S+ (Pin 8)	S- (Pin 10)	Function			
Х	0	D- = HSD1-			
Х	1	D- = HSD2-			
0	Х	D+ = HSD1+			
1	Х	D+ = HSD2+			

PIN DESCRIPTIONS				
Pin Name Description				
S+	Select Input for D+			
S-	Select Input for D-			
HSD1±, HSD2±, D±	Data Port			

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)					
Parameter		Limit	Unit		
Reference to GND	V+	- 0.3 to 5.0	V		
neierence to GND	S+, S-, D±, HSD1±, HSD2± <sup>a</sup>	- 0.3 to (V+ + 0.3)	7		
Current (Any Terminal except S+, S-, D:	30				
Continuous Current (S+, S-, D±, HSD1:	± 250	mA			
Peak Current (Pulsed at 1 ms, 10 % Duty Cycle)		± 500			
Storage Temperature (D Suffix)		- 65 to 150	°C		
Power Dissipation (Packages) <sup>b</sup> miniQFN-10 <sup>c</sup>		208	mW		
ESD (Human Body Model) I/O to GND		8	kV		
Latch-up (Current Injection)		300	mA		

## Notes:

- a. Signals on S+, S-, D±, HSD1±, HSD2± exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current
- b. All leads welded or soldered to PC board.
- c. Derate 2.6 mW/°C above 70 °C.

SPECIFICATIONS (V+ = 3.0 V)								
		Test Conditions		Limits - 40 °C to 85 °C				
Parameter	Symbol	Otherwise Unless Specified	Temp.a	Min.b	Typ.c	Max.b	Unit	
Analog Switch								
Analog Signal Range <sup>d</sup>	V <sub>ANALOG</sub>	R <sub>DS(on)</sub>	Full	0		V+	V	
On-Resistance	Book	V+ = 3.0 V, I <sub>D+</sub> = 8 mA, V <sub>HSD1/2+</sub> = 0.4 V	Room		7	8		
On-nesistance	R <sub>DS(on)</sub>	V 1 = 0.0 V, 1D± = 0 111/V, VHSD1/2± = 0.4 V	Full			9		
On-Resistance Match <sup>d</sup>	$\Delta R_{ON}$	$V+ = 3.0 \text{ V}, I_{D\pm} = 8 \text{ mA}, V_{HSD1/2\pm} = 0.4 \text{ V}$	Room		0.8		Ω	
On-Resistance Resistance Flatness <sup>d</sup>	R <sub>ON</sub> Flatness	$V+ = 3.0 \text{ V}, I_{D\pm} = 8 \text{ mA}, V_{HSD1/2\pm} = 0.0 \text{ V}, 1.0 \text{ V}$	Room		2.0			
Switch Off Leakage Current	I <sub>(off)</sub>	$V+ = 4.3 \text{ V}, V_{\text{HSD1/2}\pm} = 0.3 \text{ V}, 3.0 \text{ V},$ $V_{\text{D}\pm} = 3.0 \text{ V}, 0.3 \text{ V}$	Full	- 100		100	4	
Channel On Leakage Current	I <sub>(on)</sub>	$V+ = 4.3 \text{ V}, V_{\text{HSD1/2}\pm} = 0.3 \text{ V}, 4.0 \text{ V}, $ $V_{\text{D}\pm} = 4.0 \text{ V}, 0.3 \text{ V}$	Full	- 200		200	nA	
Digital Control								
Input Voltage High	V <sub>INH</sub>	V+ = 3.0 V to 3.6 V	Full	1.3				
приг уонаде нідп	*INH	V+ = 4.3 V	Full	1.5			V	
Input Voltage Low	V <sub>INL</sub>	V+ = 3.0 V to 4.3 V	Full			0.5		
Input Capacitance	C <sub>IN</sub>		Full		5.6		pF	
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	V <sub>IN</sub> = 0 or V+	Full	- 1		1	μΑ	



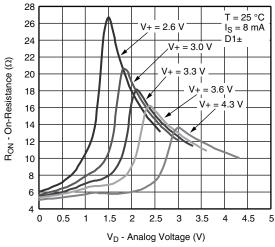
SPECIFICATIONS (V+ = 3.0 V)									
		Test Conditions		Limits - 40 °C to 85 °C		5 °C			
Parameter	Symbol	Otherwise Unless Specified	Temp.a	Min.b	Typ.c	Max.b	Unit		
Dynamic Characteristics	Dynamic Characteristics								
Break-Before-Make Time <sup>e, d</sup>	t <sub>BBM</sub>		Room Full		5				
		$V+ = 3.0 \text{ V}, V_{D1/2} + = 1.5 \text{ V}, R_1 = 50 \Omega,$	Room						
S-, S+ Turn-On Time <sup>e, d</sup>	t <sub>ON</sub>	C <sub>L</sub> = 35 pF	Full			30	ns		
0 0 T 0"T 9 d		1	Room			25			
S-, S+ Turn-Off Time <sup>e, d</sup>	t <sub>OFF</sub>		Full			25			
Charge Injection <sup>d</sup>	$Q_{INJ}$	$C_L = 1 \text{ nF, } R_{GEN} = 0 \Omega, V_{GEN} = 0 \text{ V}$			0.5		рС		
Off-Isolation <sup>d</sup>	OIRR	V+ = 3.0 V to 3.6 V, $R_L$ = 50 Ω, $C_L$ = 5 pF,			- 30		dB		
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	f = 240 MHz			- 45				
Bandwidth <sup>d</sup>	BW	V+ = 3.0 V to 3.6 V, $C_L$ = 5 pF, $R_L$ = 50 $\Omega$ , - 3 dB			700		MHz		
O. 10%O d	C <sub>D1± (off)</sub>				2.5				
Channel-Off Capacitance <sup>d</sup>	C <sub>D2± (off)</sub>	V. 00V f 4MI-	Room		2.5				
o	C <sub>D± (off)</sub>	V+ = 3.3 V, f = 1 MHz	riodin		2.5		pF		
Channel-On Capacitance <sup>d</sup>	C <sub>D± (on)</sub>				6.5				
Channel-to-Channel Skew <sup>d</sup>	t <sub>SK(O)</sub>				50				
Skew Off Opposite Transitions of the Same Output <sup>d</sup>	t <sub>SK(p)</sub>	V+ = 3.0 V to 3.6 V, $R_L$ = 50 $\Omega$ , $C_L$ = 5 pF			20		ps		
Total Jitter <sup>d</sup>	tJ				200				
Power Supply									
Power Supply Range	V+			2.6		4.3	V		
Power Supply Current	I+	$V_{IN} = 0 \text{ V, or V+}$	Full			2	μΑ		

#### Notes:

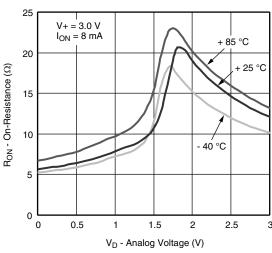
- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, not subjected to production test.
- e. V<sub>IN</sub> = input voltage to perform proper function.
- f. Crosstalk measured between channels.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

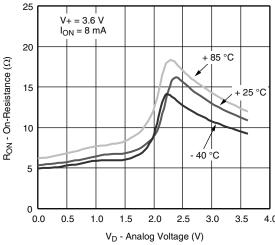
## **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



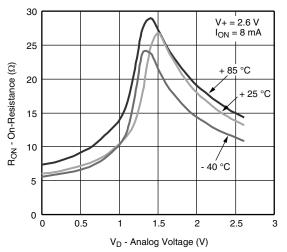
R<sub>ON</sub> vs. V<sub>D</sub> and Single Supply Voltage



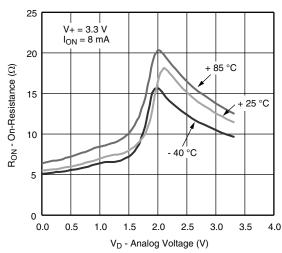
**R<sub>ON</sub> vs. Analog Voltage and Temperature** 



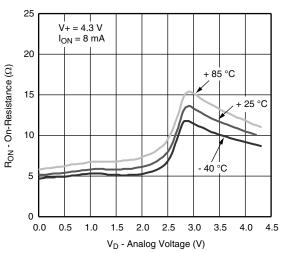
R<sub>ON</sub> vs. Analog Voltage and Temperature



R<sub>ON</sub> vs. Analog Voltage and Temperature



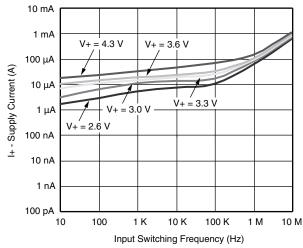
**R<sub>ON</sub> vs. Analog Voltage and Temperature** 



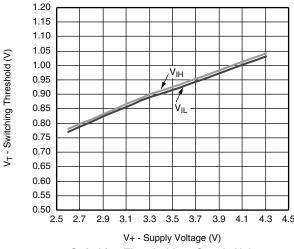
R<sub>ON</sub> vs. Analog Voltage and Temperature



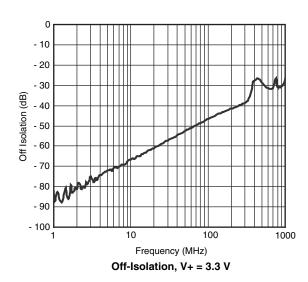
## **TYPICAL CHARACTERISTICS** $(T_A = 25 \, ^{\circ}C, \text{ unless otherwise noted})$

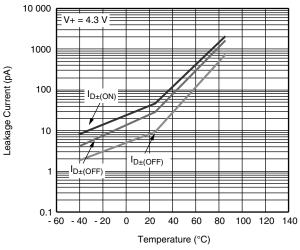


**Supply Current vs. Input Switching Frequency** 

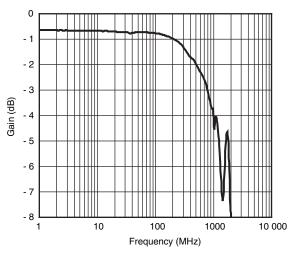


Switching Threshold vs. Supply Voltage

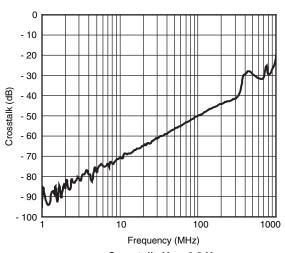




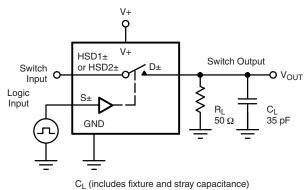
Leakage Current vs. Temperature



Gain vs. Frequency, V+ = 3.3 V



### **TEST CIRCUITS**



 $V_{\mathsf{INH}}$  $t_r < 5 \text{ ns}$ Logic 50 % < 5 ns Input  $V_{\mathsf{INL}}$  $0.9 \times V_{OUT}$ Switch Output 0 V  $t_{ON}$ 

> Logic "1" = Switch on Logic input waveforms inverted for switches that have the opposite logic sense.

 $V_{OUT} = D \pm \left( \frac{R_L}{R_L + R_{ON}} \right)$ 

Figure 1. Switching Time

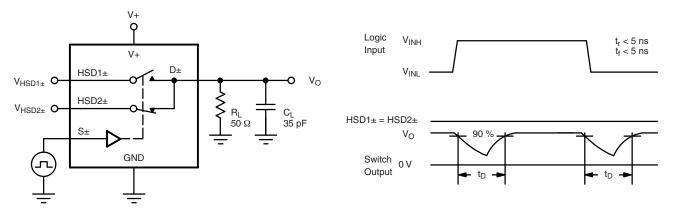


Figure 2. Break-Before-Make Interval

C<sub>L</sub> (includes fixture and stray capacitance)

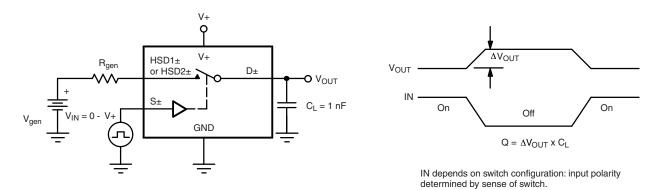


Figure 3. Charge Injection



### **TEST CIRCUITS**

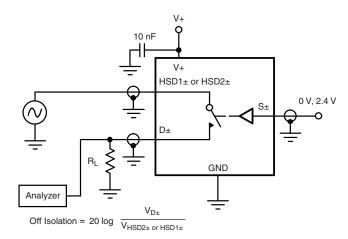


Figure 4. Off-Isolation

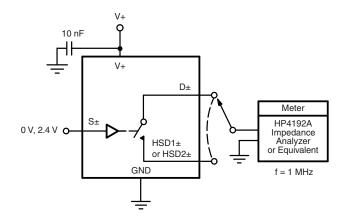
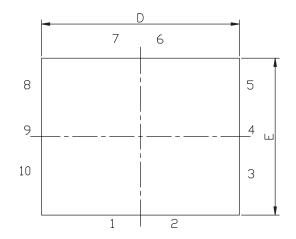
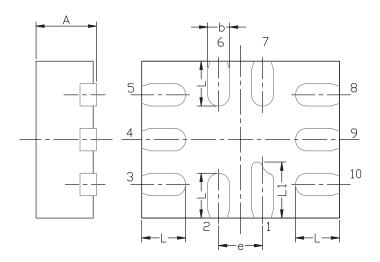


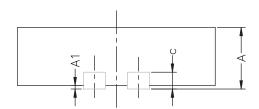
Figure 5. Channel Off/On Capacitance

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## **MINI QFN-10L CASE OUTLINE**







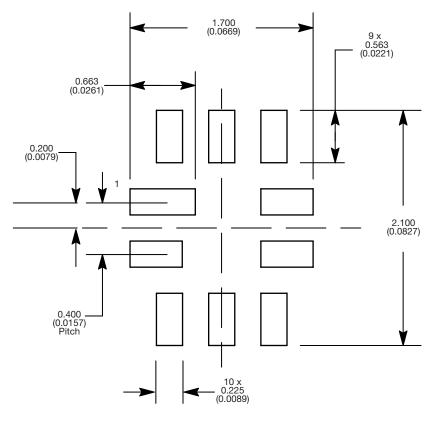
DIM	M	IILLIMETER	S	INCHES			
DIIVI	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.	
Α	0.50	0.55	0.60	0.0197	0.0217	0.0236	
A1	0.00	-	0.05	0.000	-	0.002	
b	0.15	0.20	0.25	0.006 0.008 0.010			
С	0.15 REF			0.006 REF			
D	1.75	1.80	1.85	0.069 0.071 0.073			
Е	1.35	1.40	1.45	0.053	0.055	0.057	
е		0.40 BSC		0.016 BSC			
L	0.35	0.40	0.45	0.014	0.016	0.018	
L1	0.45	0.50	0.55	0.0177	0.0197	0.0217	

ECN T-07039-Rev. A, 12-Feb-07

DWG: 5957



## **RECOMMENDED MINIMUM PADS FOR MINI QFN 10L**



Mounting Footprint Dimensions in mm (inch)



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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Revision: 02-Oct-12 Document Number: 91000